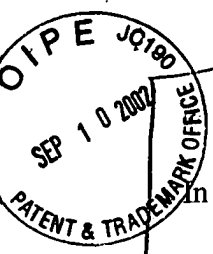


2835



**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re the Application of:

**Yusuke Kohyama et al.**

Serial No.: 09/631,830

Filed: August 3, 2000

For: STACKED CAPACITOR-TYPE  
SEMICONDUCTOR STORAGE DEVICE  
AND MANUFACTURING METHOD  
THEREOF

Atty. Docket No.: 001701.00021

Group Art Unit: 2835

Examiner: H. Duong

Confirmation No.: 9692

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**AMENDMENT**

Commissioner for Patents  
Washington, D.C. 20231

Sir:

In response to the Office Action mailed June 10, 2002, please amend the instant application as follows:

**IN THE CLAIMS:**

Please amend the claims as follows:

20. (Amended) A method of manufacturing a semiconductor storage device comprising the steps of:

forming a first insulating film on a semiconductor substrate;

forming a conductive film on said first insulating film;

forming a protective film on said conductive film;

etching said protective film and said conductive film locally and forming first and second wirings;

forming a second insulating film between said first and second wirings;

etching said second insulating film and said first insulating film locally by using said protective film as a mask and forming a contact hole between said first and second wirings; and

forming a third insulating film at least on a side wall of said conductive film and on a side wall of said first insulating film in said contact hole, wherein said third insulating film is in

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